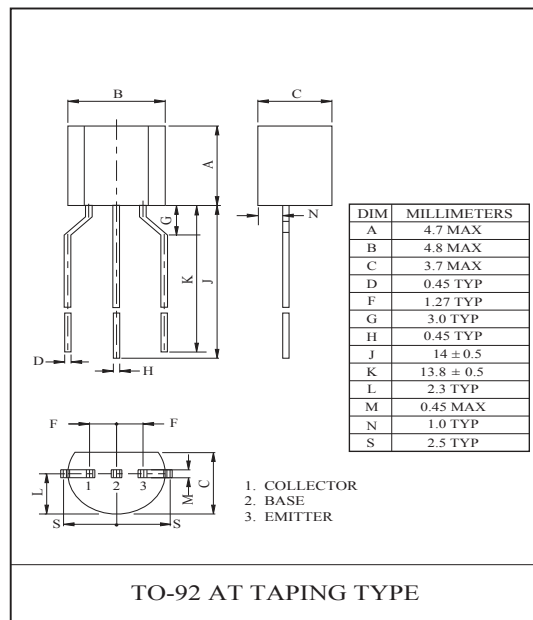
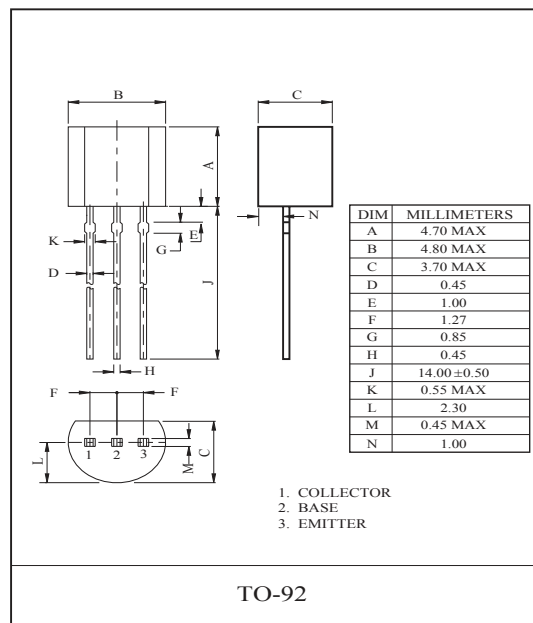


GENERAL PURPOSE HIGH DARLINGTON TRANSISTOR.

MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	10	V
Collector Current	I_C	500	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 ~ 150	°C

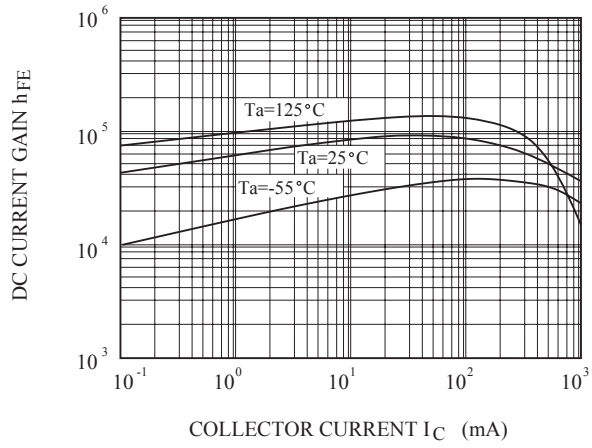


ELECTRICAL CHARACTERISTICS (Ta=25°C)

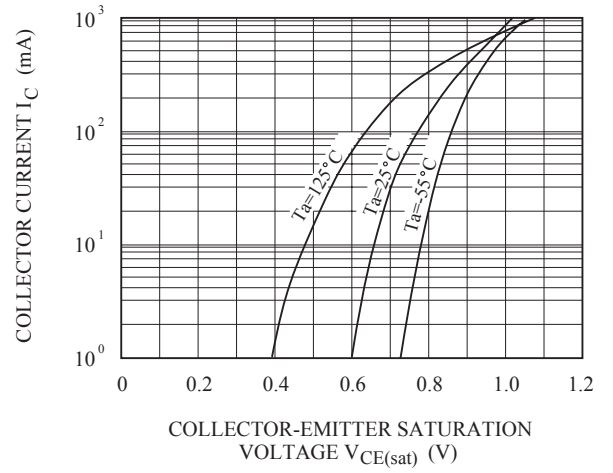
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=0.1mA, I_E=0$	40	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	30	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1.0mA, I_C=0$	10	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB}=40V, I_E=0$	-	-	1.0	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=10V, I_C=0$	-	-	1.0	μA
DC Current Gain	h_{FE}	$I_C=100mA, V_{CE}=2V$	30k	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=100mA, I_B=1mA$	-	-	1.0	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=100mA, I_B=1mA$	-	1.5	2.0	V
Current Gain Bandwidth Product	f_T	$I_C=100mA, V_{CE}=2V, f=100MHz$	-	220	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, f=1MHz, I_E=0$	-	5.0	-	pF

BC517

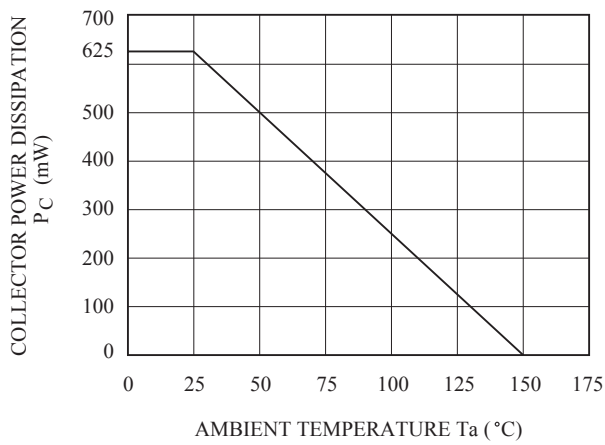
$h_{FE} - I_C$



$I_C - V_{CE(sat)}$



$P_C - T_a$



$I_C - V_{BE}$

